Correction to: High-Voltage Superconducting Fault Current Limiters Based on High-Diffusivity Dielectric Substrates

Guy Deutscher¹

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The original version of this article contains the following mistakes:

On the second page 1st paragraph under heading “The Role of the Substrate Diffusivity” second and third sentences, 90 K, 300 cm²/s and 5 mm, should be replaced with 65 K, 100 cm²/s and 3 mm, respectively. Still on the same page, under heading “Maximum Power”, 0.5 cm and 15,000 W/cm² should be replaced with 0.3 cm and 9000 W/cm², respectively. Corrected sentences should read:

At 65 K, the critical temperature of the HTS layer, its value is about 100 cm²/s. If a hot spot develops because of

the presence of some defect in the HTS layer, within 1 ms, the temperature increase of the substrate is smoothed out over the length scale $\delta = 3$ mm, which is of the order of a typical tape width.

Taking a value of 1 J/cm³, and $\delta = 0.3$ cm, we get a maximum power of 9000 W/cm².

Also, on the third page last sentence under heading “Shunt Optimization for Achieving Highest Possible Electric Field”, 5 kV/m should be replaced with 3 kV/m. Corrected sentence should read:

For a critical current of 300 A/cm-w, the maximum electric field that can be achieved will be 3 kV/m for a sapphire-based tape and 130 V/m for a Hastelloy-based tape.

The original article has been corrected.

The online version of the original article can be found at <https://doi.org/10.1007/s10948-018-4633-8>.

✉ Guy Deutscher
guyde@tau.ac.il

¹ School of Physics and Astronomy, Tel Aviv University, Ramat Aviv, 69978 Tel Aviv, Israel